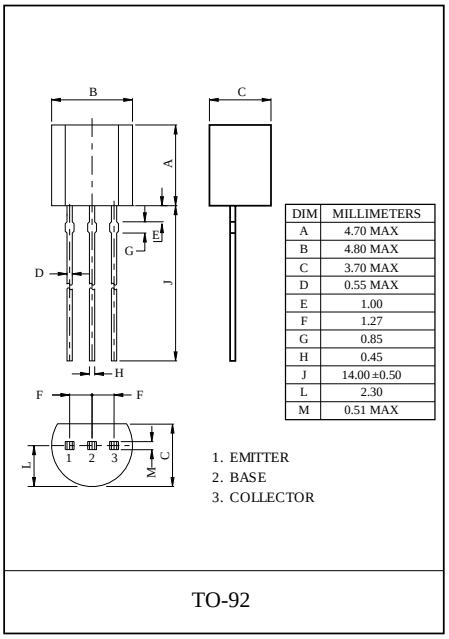
MPSA94 TRANSISTOR (PNP)



DIM	MILLIMETERS
A	4.70 MAX
B	4.80 MAX
C	3.70 MAX
D	0.55 MAX
E	1.00
F	1.27
G	0.85
H	0.45
J	14.00 ±0.50
L	2.30
M	0.51 MAX

TO-92

FEATURES

- High Breakdown Voltage

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-400	V
V_{CEO}	Collector-Emitter Voltage	-400	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current	-0.3	A
P_C	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	200	℃/W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55 ~ 150	℃

ELECTRICAL CHARACTERISTICS (T =25 unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-100μA I_E=0	-400			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-1.0mA I_B=0	-400			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=-100μA I_C=0	-5.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-300V I_E=0			-0.1	μA
Collector Cut-Off Current	I_{CEO}	V_{CE}=-400V I_E=0			-5.0	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-4.0V I_C=0			-0.1	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=-10V I_C=-10mA	80		300	
	$h_{FE(2)}$	V_{CE}=-10V I_C=-1.0mA	70			
	$h_{FE(3)}$	V_{CE}=-10V I_C=-100mA	40			
Collector to Emitter Saturation Voltage	$V_{CE(sat)(1)}$	I_C=-10mA I_B=-1.0mA			-0.2	V
	$V_{CE(sat)(2)}$	I_C=-50mA I_B=-5.0mA			-0.3	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=-10mA I_B=-1.0mA			-0.75	V
Transition Frequency	f_T	V_{CE}=-5.0V I_C=-10mA f=30MHz	50			MHz

Electrical Characteristic Curve